

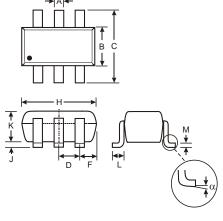


DMMT5551/DMMT5551S

MATCHED NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DMMT5401)
- Ideal for Low Power Amplification and Switching
- Intrinsically Matched NPN Pair (Note 1)
- 2% Matched Tolerance, h_{FE}, V_{CE(SAT)}, V_{BE(SAT)}
- Lead Free/RoHS Compliant (Note 4)
- "Green" Device (Note 5 and 6)



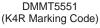
	SOT-26											
Dim	Min	Max	Тур									
Α	0.35	0.50	0.38									
В	1.50	1.70	1.60									
С	2.70	3.00	2.80									
D			0.95									
F			0.55									
Н	2.90	3.10	3.00									
J	0.013	0.10	0.05									
K	1.00	1.30	1.10									
L	0.35	0.55	0.40									
M	0.10	0.20	0.15									
	0°	8°										
All Dimensions in mm												

Diodes Incorporated

Mechanical Data

- Case: SOT-26
- Case Material: Molded Plastic, "Green" Molding Compound, Note 7. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Copper leadframe).
- Marking (See Page 2): K4R & K4T
- Ordering & Date Code Information: See Page 2
- Weight: 0.006 grams (approximate)







DMMT5551S (K4T Marking Code)

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	180	V
Collector-Emitter Voltage	V _{CEO}	160	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current - Continuous (Note 2)	Ic	200	mA
Power Dissipation (Note 2, 3)	Pd	300	mW
Thermal Resistance, Junction to Ambient (Note 2)	R _{JA}	417	°C/W
Operating and Storage and Temperature Range	T _j , T _{STG}	-55 to +150	°C

Notes: 1. Built with adjacent die from a single wafer.

- 2. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 3. Maximum combined dissipation.
- 4. No purposefully added lead.
- 5. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php..
- 6. Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

DS30436 Rev. 7 - 2 1 of 4 DMMT5551/DMMT5551S



Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition					
OFF CHARACTERISTICS (Note 7)										
Collector-Base Breakdown Voltage	V _{(BR)CBO}	180		V	$I_C = 100 \mu A, I_E = 0$					
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	160		V	$I_C = 1.0 \text{mA}, I_B = 0$					
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6.0		V	$I_E = 10\mu A, I_C = 0$					
Collector Cutoff Current	I _{CBO}		50	nA μA	V _{CB} = 120V, I _E = 0 V _{CB} = 120V, I _E = 0, T _A = 100°C					
Emitter Cutoff Current	I _{EBO}		50	nA	V _{EB} = 4.0V, I _C = 0					
ON CHARACTERISTICS (Note 7)										
DC Current Gain (Note 8)	h _{FE}	80 80 30	250		I _C = 1.0mA, V _{CE} = 5.0V I _C = 10mA, V _{CE} = 5.0V I _C = 50mA, V _{CE} = 5.0V					
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		0.15 0.20	V	I _C = 10mA, I _B = 1.0mA I _C = 50mA, I _B = 5.0mA					
Base-Emitter Saturation Voltage			1.0	V	I _C = 10mA, I _B = 1.0mA I _C = 50mA, I _B = 5.0mA					
SMALL SIGNAL CHARACTERISTICS										
Output Capacitance	C _{obo}		6.0	pF	$V_{CB} = 10V, f = 1.0MHz, I_E = 0$					
Small Signal Current Gain	h _{FE}	50	250		V _{CE} = 10V, I _C = 1.0mA, f = 1.0kHz					
Current Gain-Bandwidth Product	f⊤	100	300	MHz	V _{CE} = 10V, I _C = 10mA, f = 100MHz					
Noise Figure	NF		8.0	dB	$V_{CE} = 5.0V$, $I_{C} = 200\mu A$, $R_{S} = 1.0k$, $f = 1.0kHz$					

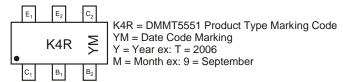
Ordering Information (Note 6 & 9)

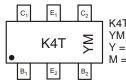
Device	Packaging	Shipping		
DMMT5551-7-F	SOT-26	3000/Tape & Reel		
DMMT5551S-7-F	SOT-26	3000/Tape & Reel		

Notes:

- 6. Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.
- 7. Short duration pulse test used to minimize self-heating effect.
 - The DC Current Gain, hFE, (matched at IC = 10mA and VCE = 5V) Collector Emitter Saturation Voltage, VCE(SAT), and Base Emitter Saturation Voltage, VBE(SAT) are matched with typical matched tolerances of 1% and maximum of 2%.
 - 9. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information





K4T = DMMT5551S Product Type Marking Code YM = Date Code Marking

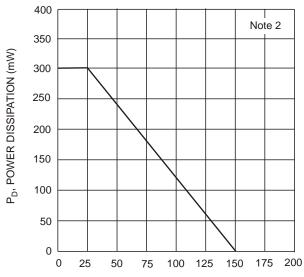
Y = Year ex: T = 2006 M = Month ex: 9 = September

Date Code Key

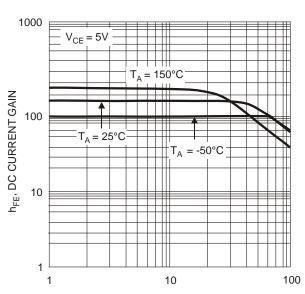
Year	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	Q	R	S	Т	U	V	W	Х	Υ	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

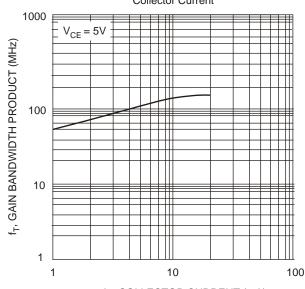




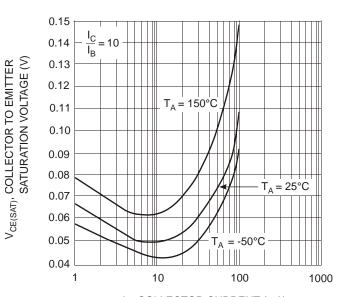
T_A, AMBIENT TEMPERATURE (°C) Fig. 1, Max Power Dissipation vs Ambient Temperature



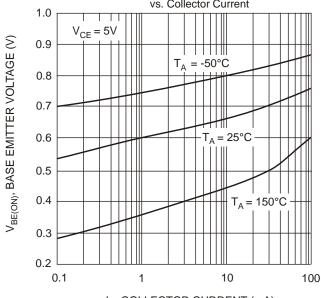
I_C, COLLECTOR CURRENT (mA) Fig. 3, DC Current Gain vs Collector Current



I_C, COLLECTOR CURRENT (mA) Fig. 5, Gain Bandwidth Product vs. Collector Current



I_C, COLLECTOR CURRENT (mA) Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current



I_C, COLLECTOR CURRENT (mA) Fig. 4, Base Emitter Voltage vs. Collector Current



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